TOSHIBA

2SC5466

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

2 S C 5 4 6 6

DYNAMIC FOCUS APPLICATIONS

HIGH VOLTAGE SWITCHING APPLICATIONS HIGH VOLTAGE AMPLIFIER APPLICATIONS

High Voltage $: V_{CEO} = 800 V$

MAXIMUM RATINGS (Ta = 25°C)

| SYMBOL | D A MILLS | |
|--------------------|--|---|
| OTMIDOL | RATING | UNIT |
| v_{CBO} | 800 | V |
| v_{CEO} | 800 | V |
| v_{EBO} | 5 | V |
| $I_{\mathbf{C}}$ | 50 | mA |
| $I_{\mathbf{B}}$ | 25 | mA |
| D | 2.0 | 777 |
| PC | 10 | W |
| T_{j} | 150 | °C |
| $T_{ m stg}$ | -55~150 | °C |
| - Sig | | |
| | V _{CEO} V _{EBO} I _C I _B P _C | $\begin{array}{c c} V_{CEO} & 800 \\ \hline V_{EBO} & 5 \\ \hline I_{C} & 50 \\ \hline I_{B} & 25 \\ \hline P_{C} & 10 \\ \hline T_{j} & 150 \\ \hline \end{array}$ |

Unit in mm BASE 2. COLLECTOR 3. EMITTER **JEDEC** EIAJ SC-67 TOSHIBA 2-10R1A

Weight: 1.7 g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

| $\begin{aligned} & \text{TEST CONDITION} \\ & \text{V}_{\text{CB}} = 640 \text{V}, \text{I}_{\text{E}} = 0 \\ & \text{V}_{\text{EB}} = 5 \text{V}, \text{I}_{\text{C}} = 0 \end{aligned}$ | MIN. | TYP. | MAX. 1.0 | UNIΊ μΑ |
|---|---|---|---|---|
| | - 12 | | 1.0 | μA |
| $V_{ED} = 5 V I_{C} = 0$ | | | | / |
| 1 LD - 4 1, LO - 4 | T-17 | a al D | 10 | μ A |
| $V_{CE} = 5 \text{ V}, I_{C} = 7 \text{ mA}$ | 15 | _ | _ | |
| $I_C = 20 \text{ mA}, I_B = 4 \text{ mA}$ | | _ | 1.0 | V |
| $I_C = 20 \text{ mA}, I_B = 4 \text{ mA}$ | - | _ | 1.5 | V |
| $V_{CE} = 10 \text{ V}, I_{C} = 3 \text{ mA}$ | _ | 5.5 | _ | MHz |
| $V_{CB} = 100 \text{ V}, \text{ f} = 1 \text{ MHz}$ | _ | 2.2 | | pF |
| | $I_{C} = 20 \text{ mA}, I_{B} = 4 \text{ mA}$ $I_{C} = 20 \text{ mA}, I_{B} = 4 \text{ mA}$ $V_{CE} = 10 \text{ V}, I_{C} = 3 \text{ mA}$ | $I_{C} = 20 \text{ mA}, I_{B} = 4 \text{ mA}$ — $I_{C} = 20 \text{ mA}, I_{B} = 4 \text{ mA}$ — $V_{CE} = 10 \text{ V}, I_{C} = 3 \text{ mA}$ — $V_{CB} = 100 \text{ V}, f = 1 \text{ MHz}$ — | $I_{C} = 20 \text{ mA}, I_{B} = 4 \text{ mA} \qquad - \qquad -$ $I_{C} = 20 \text{ mA}, I_{B} = 4 \text{ mA} \qquad - \qquad -$ $V_{CE} = 10 \text{ V}, I_{C} = 3 \text{ mA} \qquad - \qquad 5.5$ $V_{CB} = 100 \text{ V}, f = 1 \text{ MHz} \qquad - \qquad 2.2$ | $I_{C} = 20 \text{ mA}, I_{B} = 4 \text{ mA}$ — — 1.0 $I_{C} = 20 \text{ mA}, I_{B} = 4 \text{ mA}$ — — 1.5 $V_{CE} = 10 \text{ V}, I_{C} = 3 \text{ mA}$ — 5.5 — |

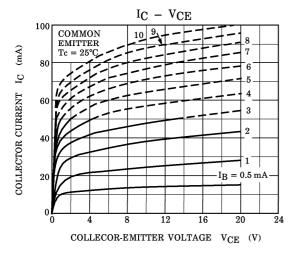
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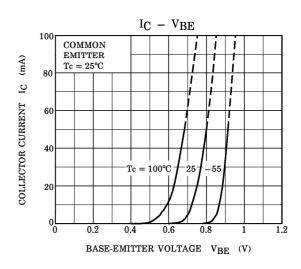
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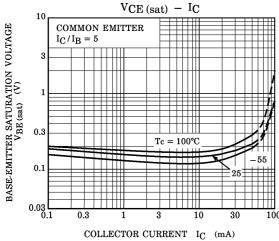
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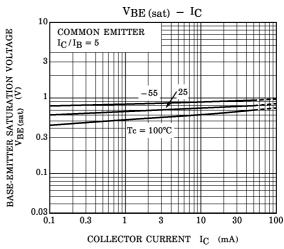
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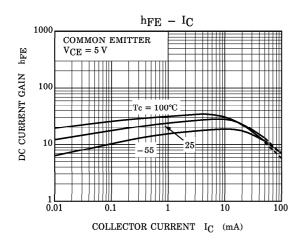
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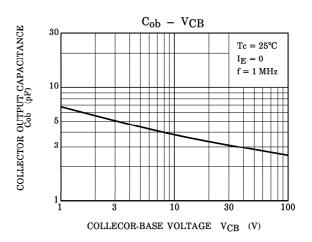












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